

CTLTVS12

SURFACE MOUNT SILICON TRANSIENT VOLTAGE SUPPRESSOR

TLP™
Tiny
Leadless
Package



Top View Bottom View

TLM2D3D6 CASE

APPLICATIONS:

- PDAs
- Memory Card Ports
- Cellular Phones
- Instrumentation



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CTLTVS12 is a low leakage, fast response TVS packaged in an ultra small, ultra low profile surface mount package. This device is designed to protect sensitive equipment against ESD damage.

MARKING CODE: O

FEATURES:

- Ultra Small, Ultra Low Profile 0.3mm x 0.6mm x 0.3mm TLP™ Leadless Surface Mount package
- Low Capacitance
- Low Leakage Current
- ESD Protection IEC 61000-4-2:
 - Air Discharge - 30kV
 - Contact Discharge - 30kV

MAXIMUM RATINGS: (T_A=25°C)

Peak Power Dissipation (8x20µs)

ESD Voltage

Operating and Storage Junction Temperature

SYMBOL

P_{PK}

V_{ESD}

T_J, T_{stg}

35

30

-55 to +150

UNITS

W

kV

°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C) V_F=1.0V MAX @ I_F=10mA

Maximum Reverse Stand-off Voltage V _{RWM}	Breakdown Voltage V _{BR} @ I _T			Test Current I _T	Maximum Reverse Leakage Current I _R @ V _{RWM}	Maximum Clamping Voltage V _C @ I _{PP}	Peak Pulse Current I _{PP}	Typical Capacitance @ 0V Bias	Typical Capacitance @ 9V Bias
V	MIN V	NOM V	MAX V	mA	µA	V	A	pF	pF
9.0	10	12	14	5.0	1.0	18	1.8	14	5.0

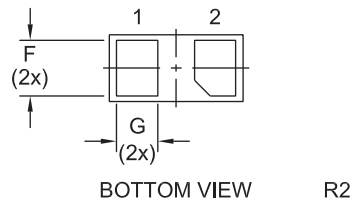
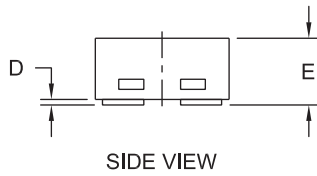
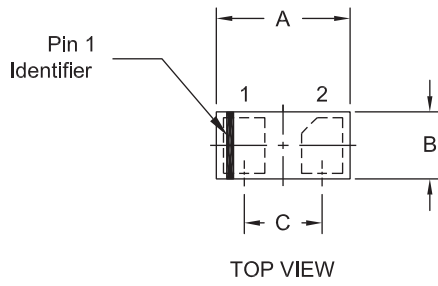
R1 (26-January 2012)

CTLTVS12

**SURFACE MOUNT SILICON
TRANSIENT VOLTAGE SUPPRESSOR**



TLM2D3D6 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.022	0.026	0.55	0.65
B	0.010	0.014	0.25	0.35
C	0.014		0.35	
D	0.000	0.002	0.00	0.05
E	0.011	0.013	0.28	0.32
F	0.008	0.012	0.20	0.30
G	0.005	0.009	0.13	0.24

TLM2D3D6 (REV: R2)

LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: O

R1 (26-January 2012)